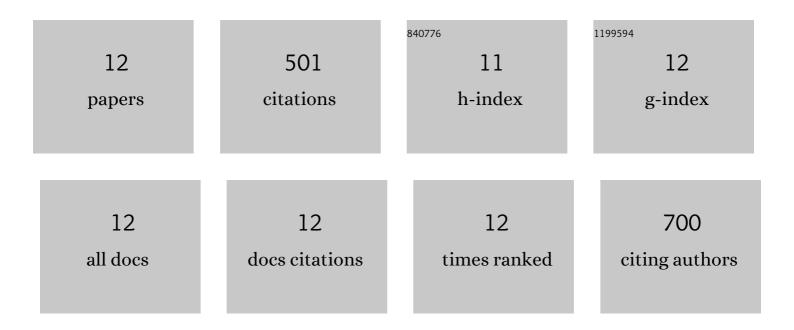
Kelsey A Mengle

List of Publications by Year in descending order

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#	Article	IF	CITATIONS
1	Toward the predictive discovery of ambipolarly dopable ultra-wide-band-gap semiconductors: The case of rutile GeO2. Applied Physics Letters, 2021, 118, .	3.3	23
2	Effect of Stacking Orientation on the Electronic and Optical Properties of Polar 2D III-Nitride Bilayers. Journal of Physical Chemistry C, 2021, 125, 16837-16842.	3.1	2
3	Thermal conductivity of rutile germanium dioxide. Applied Physics Letters, 2020, 117, 102106.	3.3	19
4	Electron and hole mobility of rutile GeO2 from first principles: An ultrawide-bandgap semiconductor for power electronics. Applied Physics Letters, 2020, 117, .	3.3	22
5	Optical properties of cubic boron arsenide. Applied Physics Letters, 2020, 116, .	3.3	29
6	Quasiparticle band structure and optical properties of rutile GeO2, an ultra-wide-band-gap semiconductor. Journal of Applied Physics, 2019, 126, .	2.5	23
7	Vibrational and electron-phonon coupling properties of β-Ga2O3 from first-principles calculations: Impact on the mobility and breakdown field. AIP Advances, 2019, 9, .	1.3	40
8	Band structure and carrier effective masses of boron arsenide: Effects of quasiparticle and spin-orbit coupling corrections. Applied Physics Letters, 2019, 114, .	3.3	46
9	Rutile GeO2: An ultrawide-band-gap semiconductor with ambipolar doping. Applied Physics Letters, 2019, 114, .	3.3	37
10	Impact of the stacking sequence on the bandgap and luminescence properties of bulk, bilayer, and monolayer hexagonal boron nitride. APL Materials, 2019, 7, .	5.1	38
11	Electronic and Optical Properties of Two-Dimensional GaN from First-Principles. Nano Letters, 2017, 17, 7345-7349.	9.1	160
12	First-principles calculations of the near-edge optical properties of β-Ga2O3. Applied Physics Letters, 2016, 109, 212104.	3.3	62